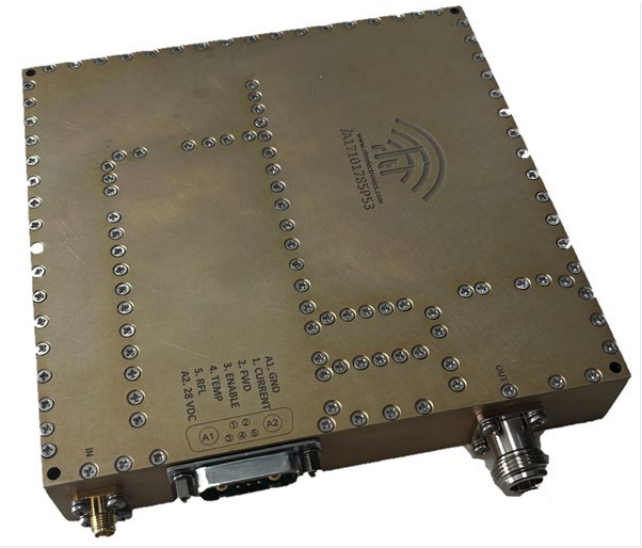
JA17101785P53; 1710 – 1785 MHz 200W AMPLIFIER

- **Solid-state Class AB design**
- **GaN on SiC Transistors**
- **High reliability and ruggedness**
- **Forward/Reflected Power Monitorings**
- **Fast Switching Capability**



ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

Frequency:	1710 - 1785 MHz
Output Power:	200 W typ., 180W min.
RF input for Rated Output:	-6 dBm typ.
Nominal Gain:	59 dB typ.
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1 (Fully Protected)
DC Supply Voltage:	28 V
DC Current:	16 A Avg typ.
Enable Speed:	5 µs max.
Operating Case Temp.:	-40 ºC to 85 ºC External Heatsink Required
Storage Temperature:	-40 ºC to 85 ºC

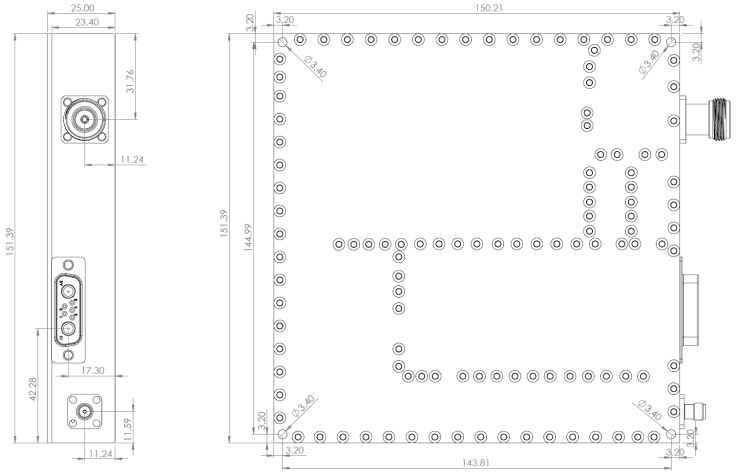
INTERFACES

RF Input:	SMA Female
RF Output:	N Female
7-PIN DSUB:	A1) GND A2) 28V 1) Current * 2) Forward Power 3) Enable (Active Low) 4) Temperature ** 5) Reverse Power

* Ampere(A) = [Voltage(mV) – 100] / 120
** Temp(°C) = [Voltage(mV) – 1000] / 20

MECHANICAL SPECIFICATIONS

Size (mm) :	150.2 x 151.4 x 25
Weight :	925 gr.
Plating :	Yellow Chromate



GENERAL DESCRIPTION

RFTR's JA17101785P53 is a reliable ultrawide-band 200W power amplifier operating between 1710-1785 MHz and suitable for CW or Pulsed waveforms. This amplifier can be used in different applications such as radars, datalinks, mobile jamming or UAVs. JA17101785P53 offers forward-reverse power monitoring and survives under ∞:1 load VSWR condition. The PA can be enabled/disabled as fast as 5 µs that makes it suitable for power saving during pulsed applications.

JA17101785P53 is designed with the components that do not require any export license.